

Docket No.: GR99P3456

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : HARALD KUHN ET AL.
Filed : CONCURRENTLY HEREWITH
Title : METHOD FOR THE SUBLIMATION GROWTH OF AN SIC
SINGLE CRYSTAL, INVOLVING HEATING UNDER GROWTH
PRESSURE



INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

German published Non-Prosecuted Patent Application DE 32 30 727 A1 (Ziegler), dated February 23, 1984, method to produce silicon carbide;

German Patent Application DE 32 30 727 C2 (Ziegler), dated February 23, 1984, method to produce single crystals from silicon carbide SIC;

European Patent Application 0 389 533 B1 (Davis et al.), dated October 3, 1990;

✓ Patent Abstracts of Japan 09 142 995 A (Noboru et al.), dated June 3, 1997;

✓ Patent Abstracts of Japan 10 182 296 A (Noboru et al.), dated July 7, 1998;

✓ Patent Abstracts of Japan 11 060 390 (Yasuo), dated March 2, 1999;

Yoo, W. et al.: "Bulk Crystal Growth of 6H-SiC on Polytype-Controlled Substrates Through Vapor Phase and Characterization", Elsevier Science Publishers B.V., 1991, pp. 733-739;

— Takahashi, J. et al.: "Influence of the Seed Face Polarity on the Sublimation Growth of α -SiC", Jpn. J. Appl. Phys., Vol. 34, Part 1, No. 9A, September 1995, pp. 4694-4698;

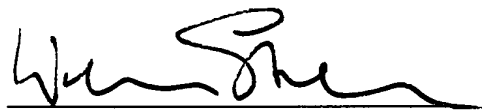
— Jayatirtha, H. et al.: "Improvement in the Growth Rate of Cubic Silicon Carbide Bulk Single Crystals grown by the sublimation Method", Elsevier Science B.V., 1997, pp. 662-668;

Ohtani, N. et al.: "Development of Large Single-Crystal SiC Substrates", Scripta Technica, 1998, pp. 8-17;

International Search Report, dated July 7, 1999;

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,



For Applicants

Date: January 7, 2002

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